

	Type	Hits	Search Text	DBs
1	BRS	1208348	sio? or "sio.sub.2" or oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	1854	("L" or L near (shap\$4 or form\$4)) near4 spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	153605	mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	4638	(sio? or "sio.sub.2" or oxide ) near8 (liner or conformal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	14	((("L" or L near (shap\$4 or form\$4)) near4 spacer) same ((sio? or "sio.sub.2" or oxide ) near8 (liner or conformal\$4)) and (mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	9006	(second! or another or additional\$4 or further) near4 (inplant or implant or implanting or implanting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	39	((("L" or L near (shap\$4 or form\$4)) near4 spacer) and ((second! or another or additional\$4 or further) near4 (inplant or implant or implanting or implanting)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search T xt	DBs
8	BRS	37	((("L" or L near (shap\$4 or form\$4)) near4 spacer) and ((second! or another or additional\$4 or further) near4 (implant or implant or implanting or implanting))) not (((("L" or L near (shap\$4 or form\$4)) near4 spacer) same ((sio? or "sio.sub.2" or oxide ) near8 (liner or conformal\$4)) and (mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet ))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	37	((("L" or L near (shap\$4 or form\$4)) near4 spacer) and ((second! or another or additional\$4 or further) near4 (implant or implant or implanting or implanting))) not (((("L" or L near (shap\$4 or form\$4)) near4 spacer) same ((sio? or "sio.sub.2" or oxide ) near8 (liner or conformal\$4)) and (mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet ))) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	153605	mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	132073	(source or drain) same (boron or B or "bf.sub.2" or indium) same (arsenic or as or phosphorus or p or antimony or sb)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	363	(source or drain) near8 (boron or B or "bf.sub.2" or indium) near8 (arsenic or as or phosphorus or p or antimony or sb) near8 (concentration or dosage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	1097	(source or drain) near8 (boron or B or "bf.sub.2" or indium) near8 (concentration or dosage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	S arch Text	DBs
14	BRS	4627	(source or drain) near8 (arsenic or as or phosphorus or p or antimony or sb) near8 (concentration or dosage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	409	((source or drain) near8 (boron or B or "bf.sub.2" or indium) near8 (concentration or dosage)) and ((source or drain) near8 (arsenic or as or phosphorus or p or antimony or sb) near8 (concentration or dosage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	74	(source or drain) near8 (boron or B or "bf.sub.2" or indium) near8 (concentration or dosage) near8 (kev or energy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	238	(source or drain) near8 (arsenic or as or phosphorus or p or antimony or sb) near8 (concentration or dosage) near8 (kev or energy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	18	((source or drain) near8 (boron or B or "bf.sub.2" or indium) near8 (concentration or dosage) near8 (kev or energy)) and ((source or drain) near8 (arsenic or as or phosphorus or p or antimony or sb) near8 (concentration or dosage) near8 (kev or energy))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	IS&R	183	((438/184) or (438/185) or (438/181)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB